ABSTRACT

An object of the present invention is to provide a method for etching a single wafer, which effectively realizes a high flatness of wafer and an increase in productivity thereof. In a method for etching a single wafer, a single thin disk-like wafer sliced from a silicon single crystal ingot is spun, and a front surface of the wafer is etched with an etching solution supplied thereto. In the method, a plurality of supply nozzles are disposed above and opposite to the front surface of the wafer at different portions in the radial direction of the wafer, respectively; and then one or more conditions selected from the group consisting of temperatures, kinds, and supply flow rates of etching solutions from the plurality of supply nozzles are changed.